

100V PNP SILICON LOW SATURATION TRANSISTOR IN SOT23
Features

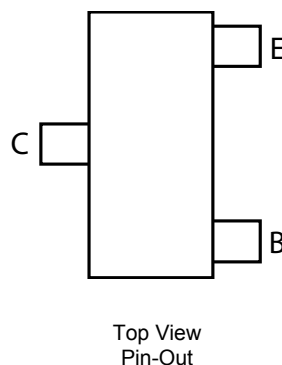
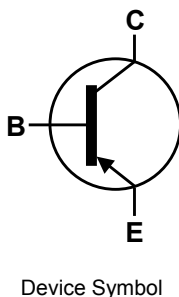
- $BV_{CEO} > -100V$
- $I_C = -1A$ Continuous Collector Current
- $I_{CM} = -2.5A$ Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < -330mV @ -1A$
- $R_{CE(sat)} = 210m\Omega$ for a low equivalent on-resistance
- 625mW power dissipation
- h_{FE} characterised up to -1.5A for high current gain hold-up
- Complementary NPN Type: FMMT624
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 Ⓔ③
- Weight 0.008 grams (approximate)

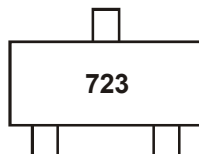
Applications

- High-side driver
- Load disconnect switch
- Motor drive


Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT723TA	723	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>

Marking Information


723 = Product Type Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	I _C	-1	A
Peak Pulse Current	I _{CM}	-2.5	A
Base Current	I _B	-500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

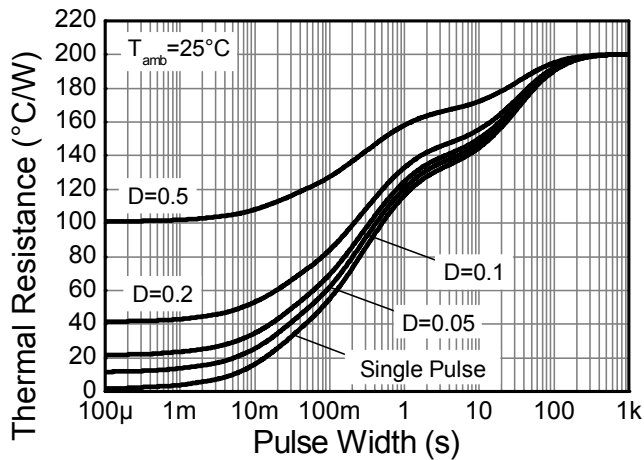
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	625	mW
Power Dissipation (Note 6)	P _D	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	155	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R _{θJL}	194	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

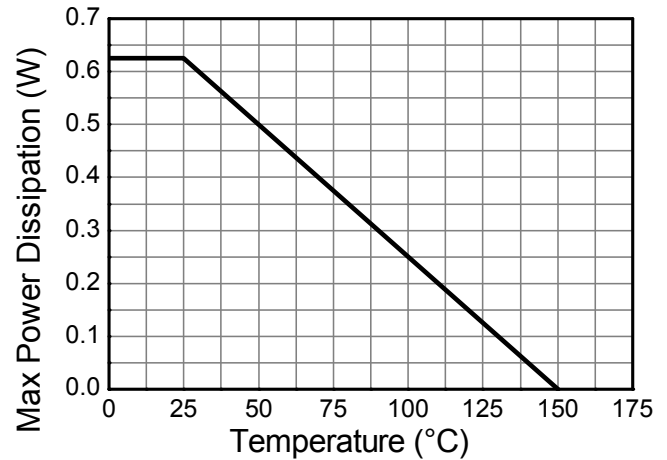
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
- For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Same as note 5, except the device is measured at t ≤ 5 sec.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

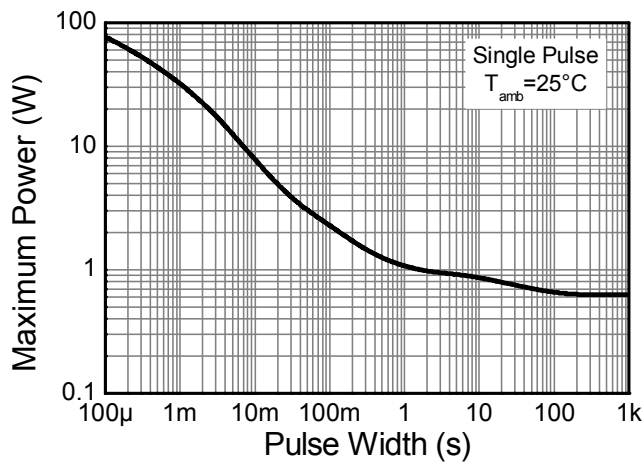
Thermal Characteristics and Derating information



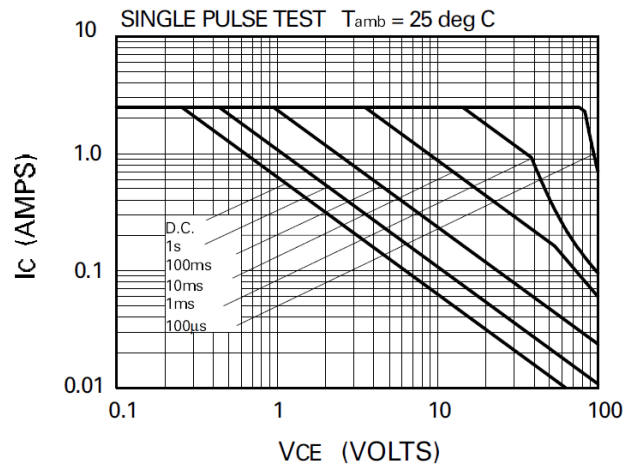
Transient Thermal Impedance



Derating Curve



Pulse Power Dissipation



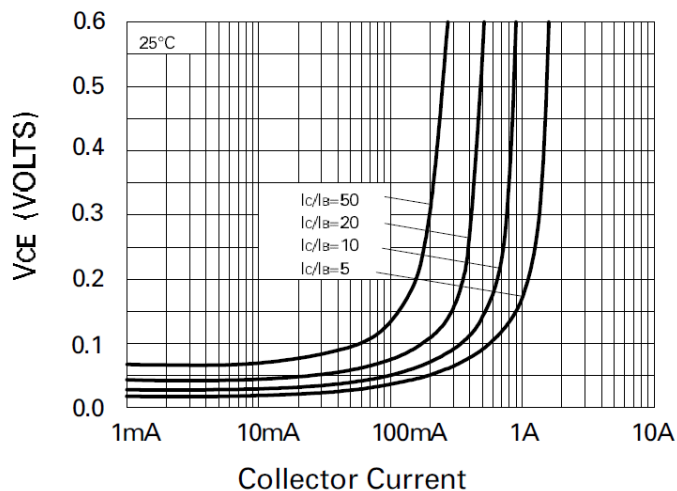
Safe Operating Area

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

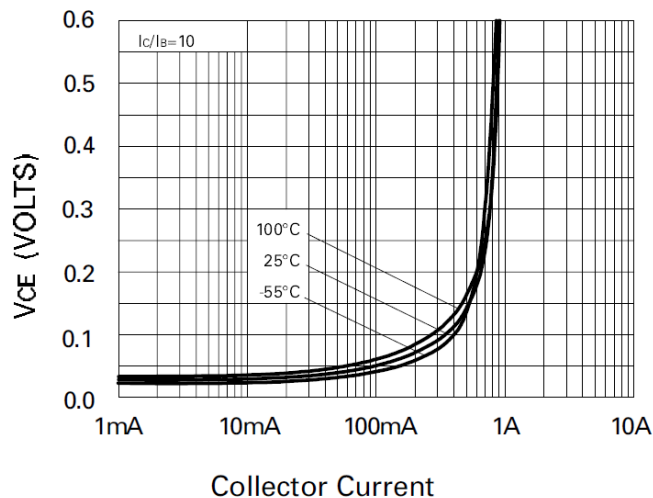
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-100	-200	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-100	-160	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.8	-	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	-	<1	-100	nA	V _{CB} = -80V
Emitter Cutoff Current	I _{EBO}	-	<1	-100	nA	V _{EB} = -5.6V
Collector Emitter Cutoff Current	I _{CES}	-	<1	-100	nA	V _{CE} = -80V
Static Forward Current Transfer Ratio (Note 9)	h _{FE}	300	475	-	-	I _C = -10mA, V _{CE} = -10V
		300	450	-		I _C = -0.1A, V _{CE} = -10V
		250	375	-		I _C = -0.5A, V _{CE} = -10V
		-	250	-		I _C = -1A, V _{CE} = -10V
		-	30	-		I _C = -1.5A, V _{CE} = -10V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}	-	-50	-80	mV	I _C = -0.1A, I _B = -10mA
		-	-125	-200		I _C = -0.5A, I _B = -50mA
		-	-210	-330		I _C = -1A, I _B = -150mA
Base-Emitter Turn-On Voltage(Note 9)	V _{BE(on)}	-	-0.71	-1.0	V	I _C = -1A, V _{CE} = -10V
Base-Emitter Saturation Voltage(Note 9)	V _{BE(sat)}	-	-0.89	-1.0	V	I _C = -1A, I _B = -150mA
Output Capacitance	C _{obo}	-	13	20	pF	V _{CB} = -10V, f = 1MHz
Transition Frequency	f _T	150	200	-	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
Turn-On Time	t _{on}	-	50	-	ns	V _{CC} = -50V, I _C = -0.5A
Turn-Off Time	t _{off}	-	760	-	ns	I _{B1} = I _{B2} = -50mA

Notes: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

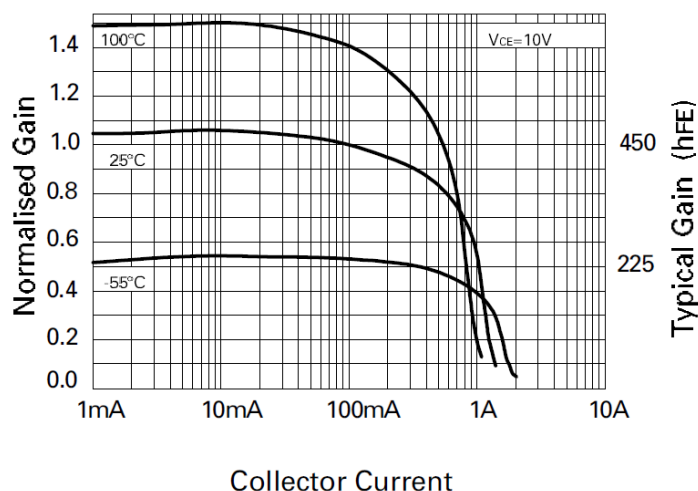
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



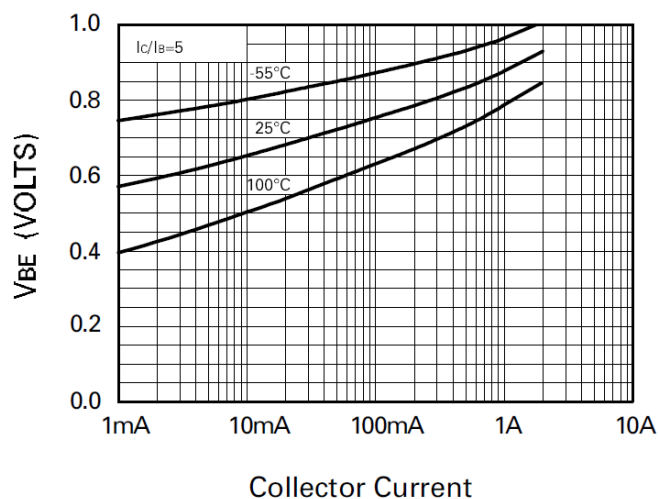
V_{CE}(SAT) vs I_C



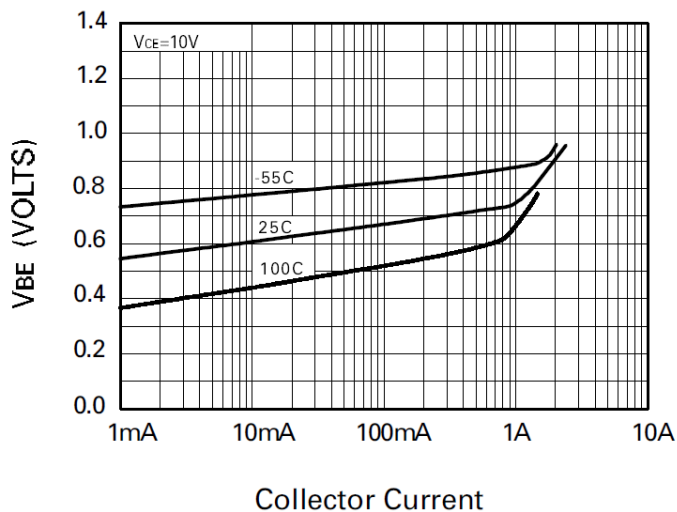
V_{CE}(SAT) vs I_C



h_{FE} vs I_C



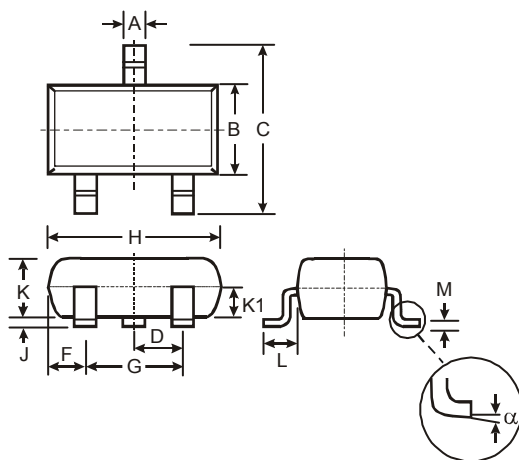
V_{BE}(SAT) vs I_C



V_{BE}(ON) vs I_C

Package Outline Dimensions

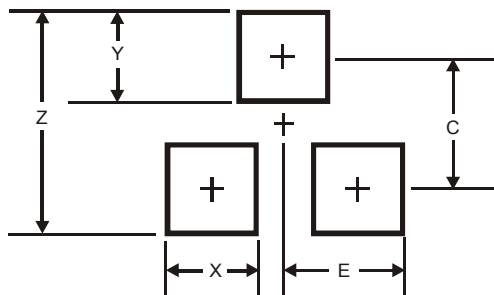
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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